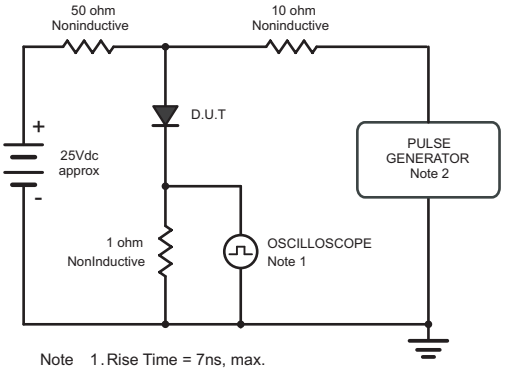
- For surface mounted applications
- Low profile package
- Glass Passivated Chip Junction
- Superfast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directives

- Case: DO-214AB/SMC
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.22g / 0.0077oz

Maximum Repetitive Peak Reverse Voltage		50	100	150	200	300	400	600	
Maximum RMS voltage		35	70	105	140	210	280	420	
Maximum DC Blocking Voltage		50	100	150	200	300	400	600	
Maximum Average Forward Rectified Current		10							
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed On Rated Load (JEDEC method)		240							
Peak Forward Surge Current,1.0ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)		480							
I^2t Rating for fusing (3msÒtÒ8.3ms)		239							
Maximum Instantaneous Forward Voltage at 10 A		1.0				1.3		1.7	
Maximum Instantaneous Reverse Current T = 25ÁC at Rated DC Reverse Voltage T = 125ÁC		10 500							
Typical Junction Capacitance(1)		280				190		100	
Maximum reverse recovery time(2)		35							
Typical Thermal Resistance(3)	R R R	37 10 13							
Operating and Storage Temperature Range	T T	-55 ~ +150							

1.Measured at 1 MHz and applied reverse voltage of 4 V D.C
2.Measured with I_F = 0.5 A, I_R = 1 A, I rr = 0.25 A.
3.P.C.B. mounted with 1.5" X 1.5" (3.81 X 3.81 cm) copper pad areas.

Fig.1 Reverse Recovery Time Characteristic And Test Circuit Diagram



Note 1. Rise Time = 7ns, max.
Input Impedance = 1megohm,22pF.
2. Ries Time =10ns, max.
Source Impedance = 50 ohms.

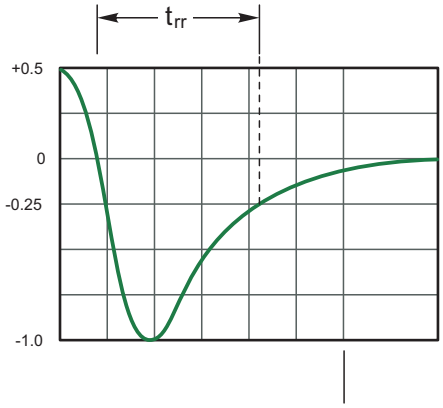


Fig.3 Typical Reverse Characteristics

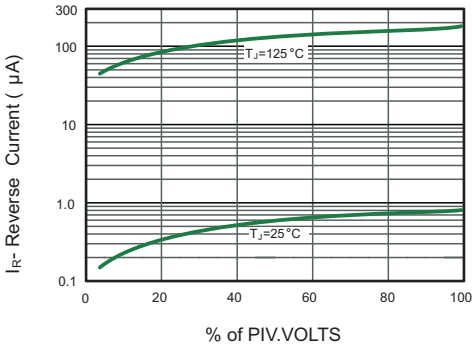


Fig.4 Typical Forward Characteristics

